N-Channel Reduced Q_g, Fast Switching MOSFET

FEATURES

- TrenchFET® Power MOSFET
- PWM Optimized for High Efficiency
- New Low Thermal Resistance PowerPAK® Package with Low 1.07-mm Profile
- 100% R_g Tested

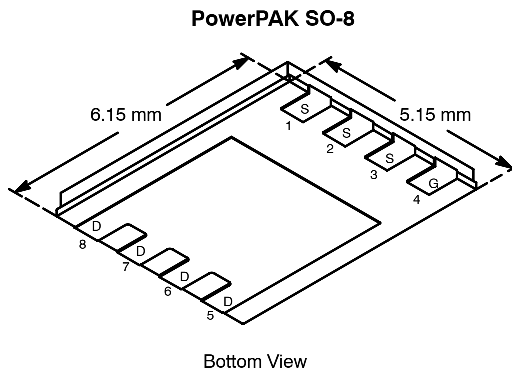
APPLICATIONS

- Buck Converter
  - High Side or Low Side
- Synchronous Rectifier
  - Secondary Rectifier

PRODUCT SUMMARY

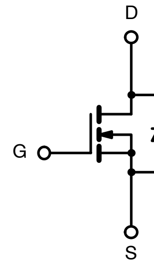
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
30	0.008 @ V_{GS} = 10 V	18
	0.011 @ V_{GS} = 4.5 V	15

PowerPAK SO-8



Bottom View

Ordering Information: Si7860DP-T1



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C UNLESS OTHERWISE NOTED)

Parameter		Symbol	10 secs	Steady State	Unit
Drain-Source Voltage		V_{DS}	30		V
Gate-Source Voltage		V_{GS}	±20		
Continuous Drain Current (T_J = 150°C)[a]	T_A = 25°C	I_D	18	11	A
	T_A = 70°C		15	8	
Pulsed Drain Current		I_{DM}	±50		
Continuous Source Current (Diode Conduction)[a]		I_S	4.1	1.5	
Avalanche Current	L= 0.1 mH	I_{AS}	30		
Single Pulse Avalanche Energy		E_{AS}	45		mJ
Maximum Power Dissipation[a]	T_A = 25°C	P_D	5	1.8	W
	T_A = 70°C		3.2	1.1	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150		°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient (MOSFET)[a]	t ≤ 10 sec	R_{thJA}	20	25	°C/W
	Steady State		56	70	
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	1.8	2.3	

Notes
a. Surface Mounted on 1" x 1" FR4 Board.

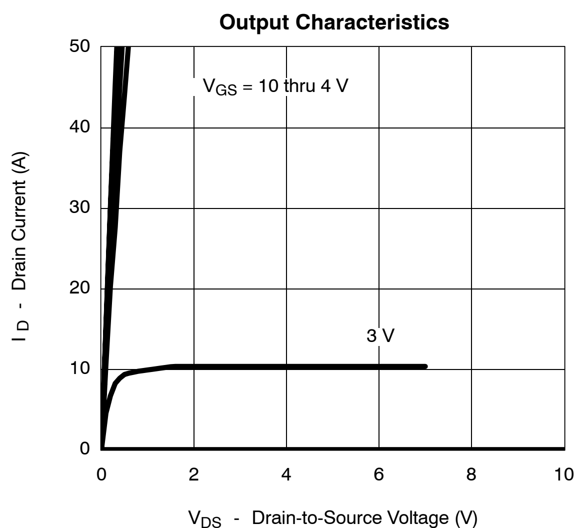
Downloaded from Elcodis.com electronic components distributor

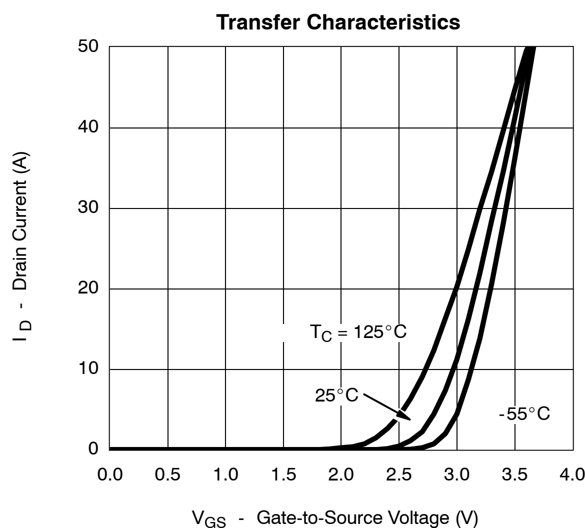
MOSFET SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 250 µA	1.0		3.0	V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 24 V, V_{GS} = 0 V			1	µA
		V_{DS} = 24 V, V_{GS} = 0 V, T_J = 70°C			5	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≥ 5 V, V_{GS} = 10 V	40			A
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 18		0.0066	0.008	Ω
		V_{GS} = 4.5 V, I_D = 15		0.0090	0.011	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 18		60		S
Diode Forward Voltage[a]	V_{SD}	I_S = 3 A, V_{GS} = 0 V		0.70	1.1	V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = 15 V, V_{GS} = 4.5 V, I_D = 18 A		13	18	nC
Gate-Source Charge	Q_{gs}			5		
Gate-Drain Charge	Q_{gd}			4.0		
Gate-Resistance	R_g		0.5	1.7	3.2	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 15 V, R_L = 15 Ω I_D ≅ 1 A, V_{GEN} = 10 V, R_G = 6 Ω		18	27	ns
Rise Time	t_r			12	18	
Turn-Off Delay Time	$t_{d(off)}$			46	70	
Fall Time	t_f			19	30	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 3 A, di/dt = 100 A/µs		40	70	

Notes
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

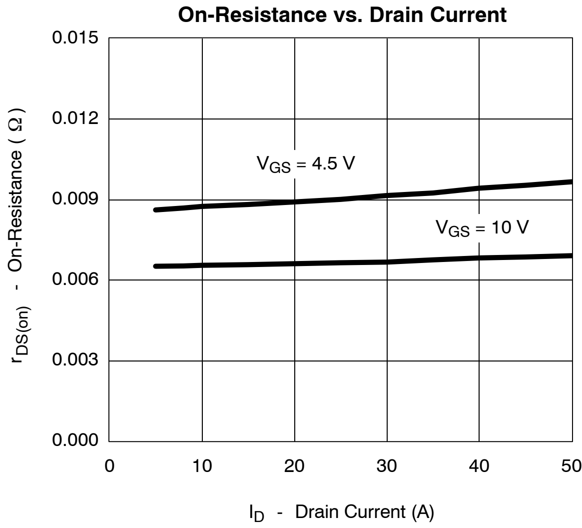


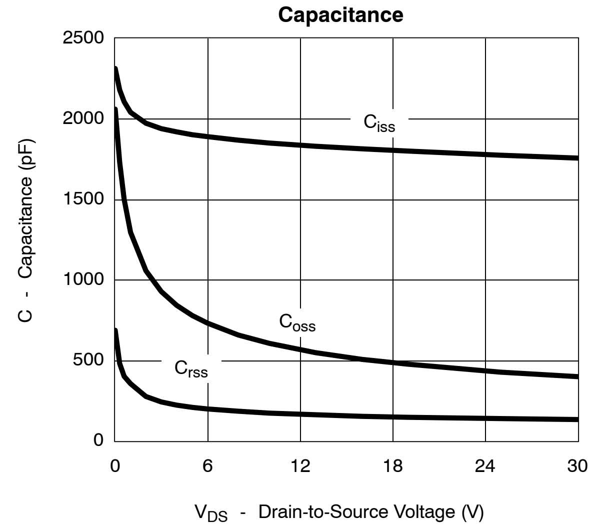


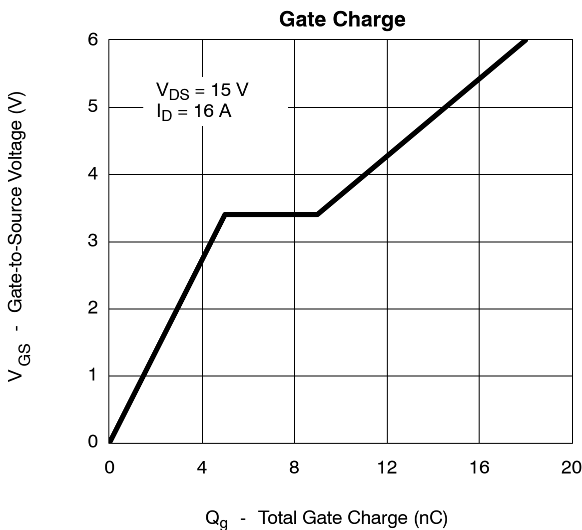
Document Number: 71854
S-32040—Rev. C, 13-Oct-03

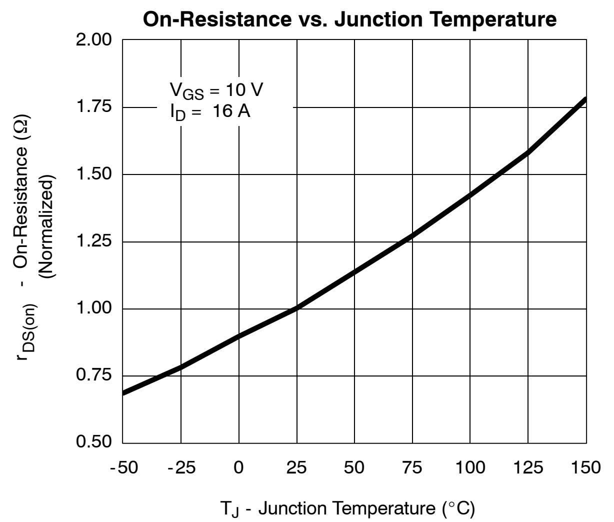
Downloaded from Elcodis.com electronic components distributor

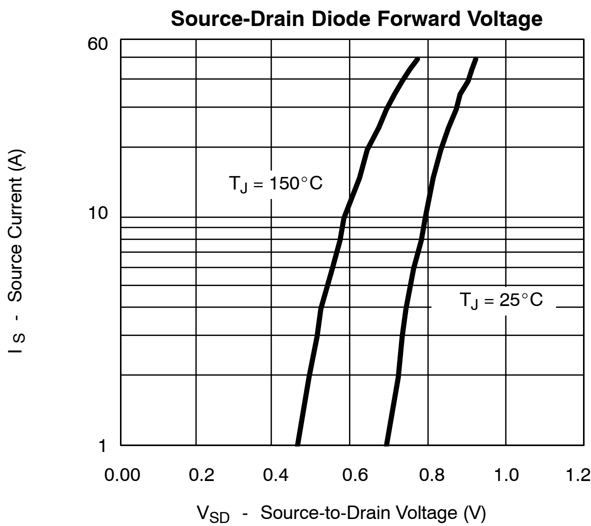
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

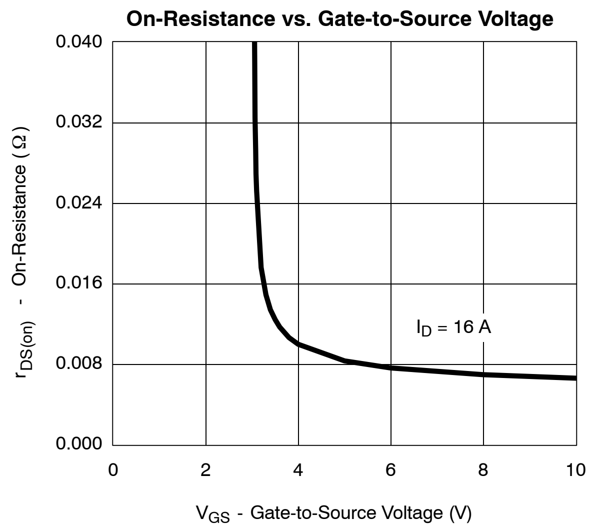








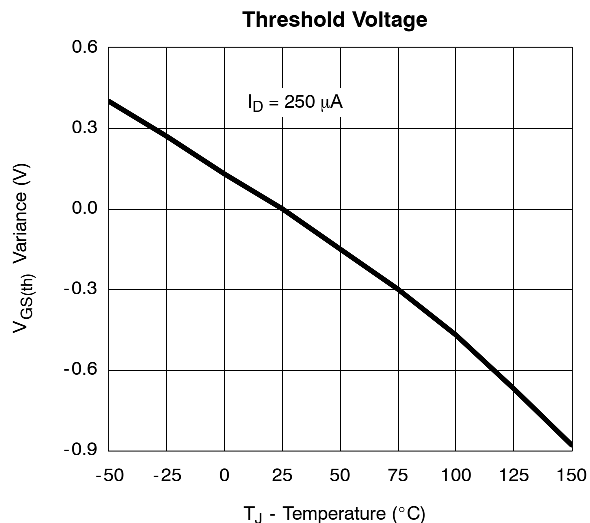


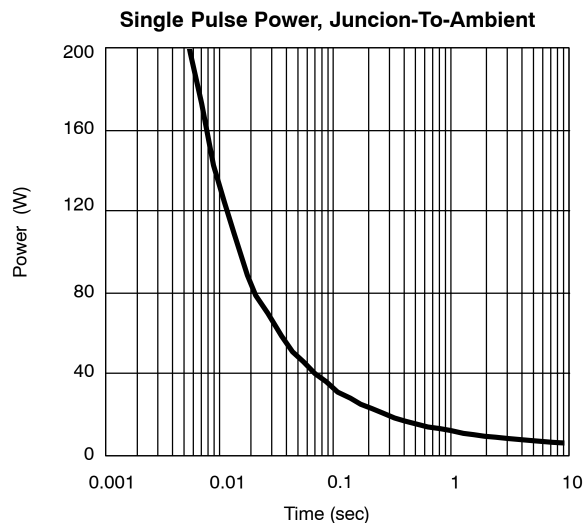


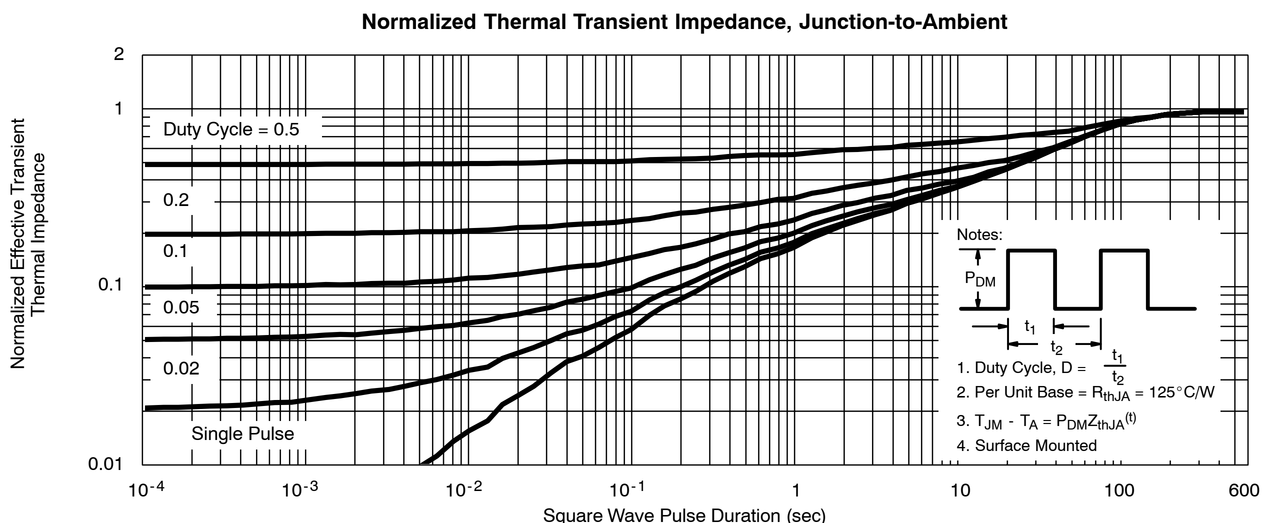
Downloaded from Elcodis.com electronic components distributor

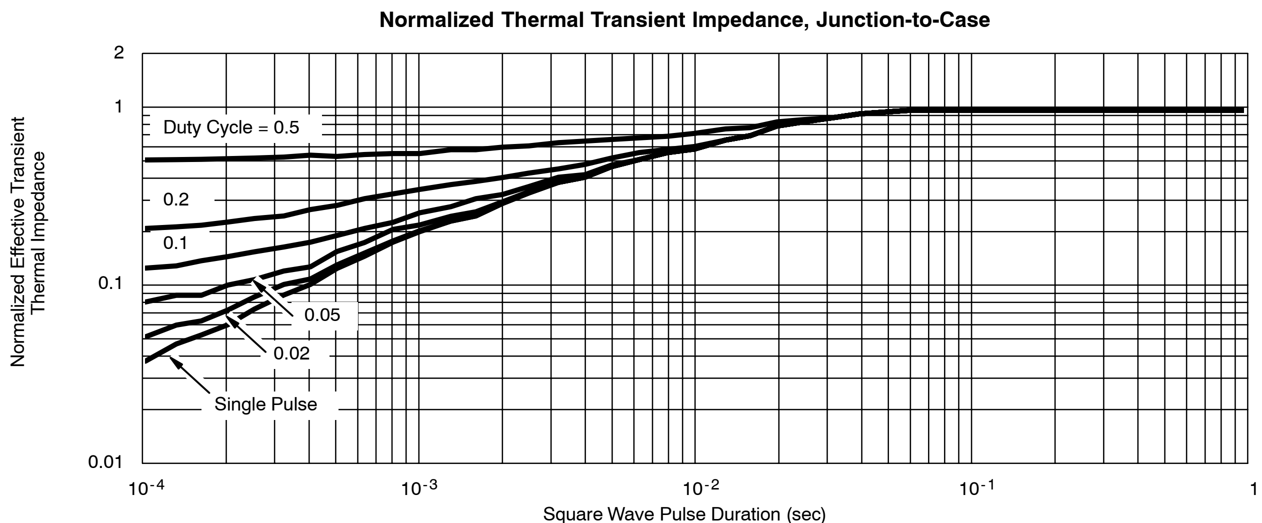
VISHAY

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)









Downloaded from Elcodis.com electronic components distributor